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#### 20V PNP SILICON LOW SATURATION TRANSISTOR IN SOT23

#### **Features and Benefits**

- BV<sub>CEO</sub> > -20V
- I<sub>C</sub> = -1A Continuous Collector Current
- I<sub>CM</sub> = -2A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -320mV @ -1A</li>
- hFE characterised up to -1.5A for high current gain hold-up
- 500mW power dissipation
- Complementary part number FMMTL618
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT-23
- UL Flammability Rating 94V-0
- Case material: molded Plastic.
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Matte Tin Finish annealed over Copper plated Alloy
   42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

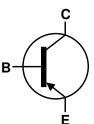
#### **Applications**

- MOSFET Gate Driving
- DC-DC Converters
- Charging circuit
- Power switches

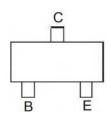
SOT23



Top View



Device Symbol



Top View Pin-Out

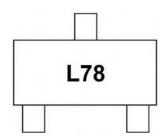
#### **Ordering Information** (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMTL718TA	L78	7	8	3,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com
- 3. For Packaging Details, go to our website at http://www.diodes.com.

## **Marking Information**



L78 = Product Type Marking Code

FMMTL718
Document Number: DS33132 Rev. 2 - 2



### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-20	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I <sub>CM</sub>	-2	Α
Base Current	I <sub>B</sub>	-200	mA

## Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 4)	$P_D$	500	mW
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{\theta JA}$	250	°C/W
Thermal Resistance, Junction to Lead	(Note 5)	$R_{ heta JL}$	197	°C/W
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C	

otes: 4. For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

5. Thermal resistance from junction to solder-point (at the end of the collector lead).

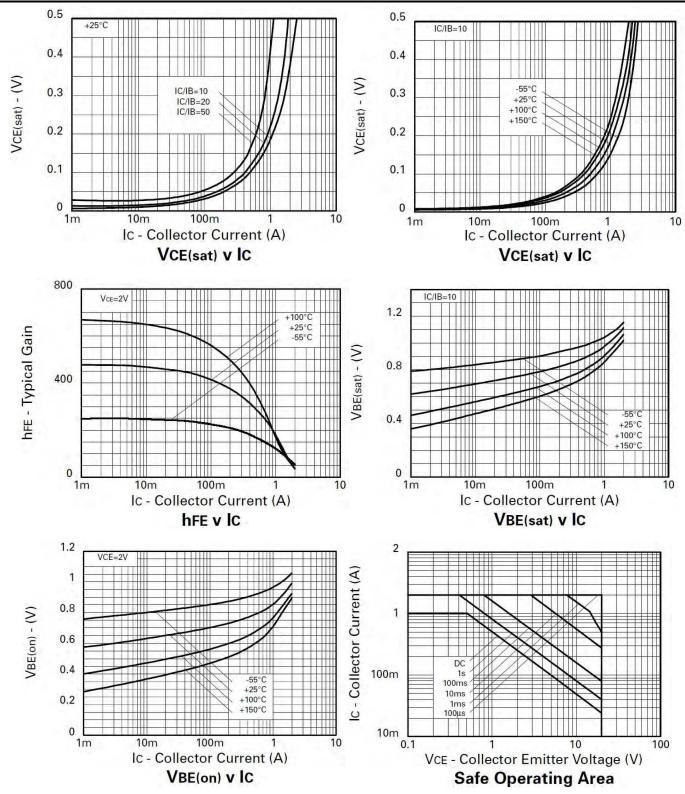
### Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-20	-65		V	$I_C = -100  \mu A$
Collector-Emitter Breakdown Voltage (Note 6)	BV <sub>CEO</sub>	-20	-55		V	I <sub>C</sub> = -10 mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	-8.8		V	I <sub>E</sub> = -100 μA
Collector Cutoff Current	I <sub>CBO</sub>			-10	nA	V <sub>CB</sub> = -15V
Emitter Cutoff Current	I <sub>EBO</sub>			-10	nA	$V_{EB} = -4V$
Collector Emitter Cutoff Current	I <sub>CES</sub>			-10	nA	V <sub>CE</sub> = -15V
Static Forward Current Transfer Ratio (Note 6)	h <sub>FE</sub>	300 300 200 120 50	500 450 320 200 80			$\begin{split} I_C &= -10 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_C &= -100 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_C &= -0.5 \text{A}, \ V_{CE} = -2 \text{V} \\ I_C &= -1 \text{A}, \ V_{CE} = -2 \text{V} \\ I_C &= -1.5 \text{A}, \ V_{CE} = -2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 6)	V <sub>CE(sat)</sub>		-33 -130 -230 -315	-50 -180 -320 -450	mV mV mV	$\begin{split} I_C = -100\text{mA}, \ I_B = -10\text{mA} \\ I_C = -500\text{mA}, \ I_B = -20\text{mA} \\ I_C = -1A, \ I_B = -50\text{mA} \\ I_C = -1.5A, \ I_B = -100\text{mA} \end{split}$
Base-Emitter Turn-On Voltage(Note 6)	$V_{BE(on)}$		-0.85	-1.0	V	$I_C = -1.25A$ , $V_{CE} = -2V$
Base-Emitter Saturation Voltage(Note 6)	V <sub>BE(sat)</sub>		-0.95	-1.1	V	I <sub>C</sub> = -1.25A, I <sub>B</sub> = -100mA
Equivalent On-Resistance	R <sub>CE(sat)</sub>		210		mΩ	$I_{C} = -1.5A$
Output Capacitance	C <sub>obo</sub>		9	12	pF	V <sub>CB</sub> = -10V, f = 1MHz
Transition Frequency	f <sub>T</sub>		265		MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Turn-On Time	t <sub>on</sub>		108		ns	V <sub>CC</sub> =-10V, I <sub>C</sub> =-1A
Turn-Off Time	t <sub>off</sub>		121		ns	$I_{B1} = I_{B2} = -10\text{mA}$

Note: 6. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%

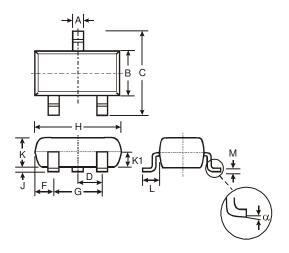


### **Typical Electrical Characteristics**



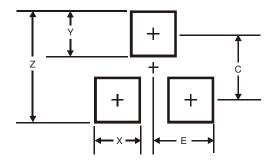


## **Package Outline Dimensions**



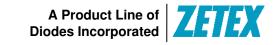
SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	1	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All	All Dimensions in mm				

## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
Е	1.35





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